## AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of forming a microcrystalline silicon thin film, comprising:

supplying, during a first process, a first gas and a second gas to a chamber in which a substrate is located;

supplying, during a second process, the second gas but not the first gas to the chamber;

depositing a portion of the microcrystalline silicon thin film during the second process; and

performing the first process and second process a plurality of times to form the microcrystalline silicon thin film having a target film thickness on the substrate.

2. (Original) The method of claim 1, wherein supplying the first gas comprises supplying $SiH_4$, and supplying the second gas comprises supplying $H_2$.

3. (Original) The method of claim 2, wherein performing the first process and second process a plurality of times is performed without removing the substrate from the chamber.

4. (Original) The method of claim 3, further comprising applying an electric field in the chamber to break down the $SiH_4$ to $SiH_2$.

5. (Previously Presented) The method of claim 4, wherein supplying the $H_2$ comprises supplying the $H_2$ at a generally constant rate, and wherein supplying the $SiH_4$ comprises supplying the $SiH_4$ at a first rate during the first process but not supplying the $SiH_4$ during the second process.

6. (Original) The method of claim 4, further comprising depositing the $SiH_2$ to a surface of the substrate during the second process.

7. (Original) The method of claim 1, further comprising:
converting the first gas to a third gas; and
depositing the third gas on the substrate during the second process.

8. (Original) The method of claim 7, wherein depositing the third gas on the substrate during the second process without supplying the first gas reduces formation of a polymer of the third gas prior to depositing of the third gas on the substrate.

9. (Previously Presented) A method of forming a microcrystalline thin film by activating a first source gas containing an element that forms a polymer when a plurality of molecules of the element are bonded in a vapor phase, and forming a film having a microcrystalline structure primarily composed of said element on a film forming target object, wherein activating the first source gas comprises applying an electric field to break down the first source gas to a second gas, the method further comprising:
performing a source supplying process in which said first source gas is supplied, and
performing a source depositing process in which the supply of said first source gas is stopped and said second gas is deposited on the film forming target object to form the microcrystalline structure.

10. (Previously Presented) The method of claim 9, wherein bonding of the second gas is suppressed in the source depositing process.

11. (Previously Presented) The method of claim 9, wherein a third gas that does not form a polymer when bonding with itself in the vapor phase is supplied in said source supplying process and said source depositing process.

12. (Previously Presented) The method of claim 11, wherein the third gas is supplied at a constant flow rate throughout said source supplying process and said source depositing process.

13. (Previously Presented) The method of claim 11, wherein a flow rate ratio, r, of said first source gas and said third gas satisfies
$r \geq -(7/12)xP+72.5$, where P is an electric field intensity density irradiated on said first source gas and said third gas.

14. (Previously Presented) The method of claim 9, wherein performing said source supplying process comprises performing the source supplying process for 2 seconds or less, and performing said source depositing process comprises performing said source depositing process for longer than said source supplying process.

15. (Previously Presented) The method of claim 11, wherein said first source gas contains $SiH_4$ and said third gas contains $H_2$.

16. (Previously Presented) The method of claim 15, wherein $SiH_4$ contained in said first source gas is broken down to $SiH_2$ in response to the electric field, the second gas comprising $SiH_2$.

17. (Original) A method of manufacturing a thin film transistor comprising:
forming a gate electrode on the substrate;
forming an insulation layer film on said substrate and said gate electrode,
forming at least a portion of a channel layer film on said insulation layer by using the microcrystalline thin film forming method of claim 9; and
forming a source/drain electrode on said channel layer.

18. (Previously Presented) The method of manufacturing a thin film transistor of claim 17, wherein forming the channel layer film comprises forming the microcrystalline thin film up to 1 nm away into the channel layer film from the interface with said insulation layer.

19.-25. (Cancelled)

26. (Previously Presented) The method of claim 1, wherein supplying the first gas and second gas during the first process comprises supplying the first gas at a first rate and the second gas at the second rate, the first rate and second rate defining a flow rate ratio that prevents a thin film formed on the substrate from becoming amorphous.

27. (Previously Presented) The method of claim 26, further comprising applying an electric field during the first process, the electric field set at an intensity that in combination with the flow rate ratio prevents a thin film formed on the substrate from becoming amorphous.

28. (Previously Presented) The method of claim 9, further comprising supplying a third gas during the source supplying process and during the source depositing process, the first source gas and the third gas being supplied at flow rates during the source supplying process to prevent a film formed on the film forming target object from becoming amorphous.

29. (Currently Amended) A method of forming a microcrystalline silicon thin film, comprising:

supplying a first gas and second gas to a chamber in which a substrate is located; and

depositing the microcrystalline silicon thin film on the substrate, wherein prior to depositing the microcrystalline thin film, the supplying of the first gas to the chamber is stopped.

30. (Currently Amended) The method of claim 29, wherein depositing the microcrystalline silicon thin film forms a majority of the microcrystalline silicon thin film on the substrate.